74HC138-Q100; 74HCT138-Q100

3-to-8 line decoder/demultiplexer; inverting

Rev. 2 — 26 January 2015

Product data sheet

1. General description

The 74HC138-Q100; 74HCT138-Q100 decodes three binary weighted address inputs (A0, A1 and A2) to eight mutually exclusive outputs (\overline{Y} 0 to \overline{Y} 7). The device features three enable inputs (\overline{E} 1, \overline{E} 2 and \overline{E} 3). Every output will be HIGH unless \overline{E} 1 and \overline{E} 2 are LOW and E3 is HIGH. This multiple enable function allows easy parallel expansion to a 1-of-32 (5 to 32 lines) decoder with just four '138' ICs and one inverter. The '138' can be used as an eight output demultiplexer by using one of the active LOW enable inputs as the data input and the remaining enable inputs as strobes. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Complies with JEDEC standard no. 7A
- Input levels:
 - For 74HC138-Q100: CMOS level
 - ◆ For 74HCT138-Q100: TTL level
- Demultiplexing capability
- Multiple input enable for easy expansion
- Ideal for memory chip select decoding
- Active LOW mutually exclusive outputs
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - \bullet MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

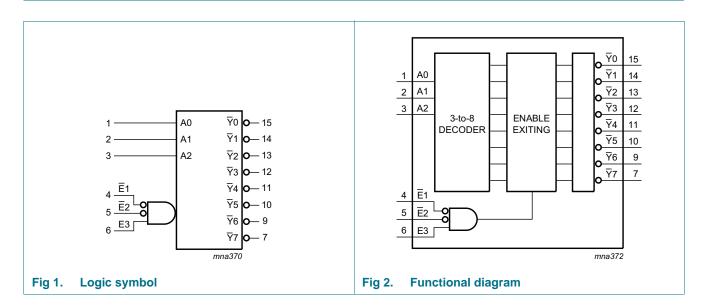


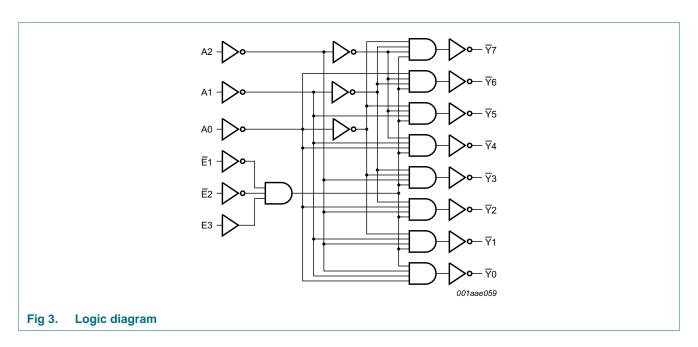
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC138D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1
74 HCT138D-Q100	-		body width 3.9 mm	
74HC138PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package;	SOT403-1
74HCT138PW-Q100	-		16 leads; body width 4.4 mm	
74HC138BQ-Q100	-40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced	SOT763-1
74HCT138BQ-Q100	- -		very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm	

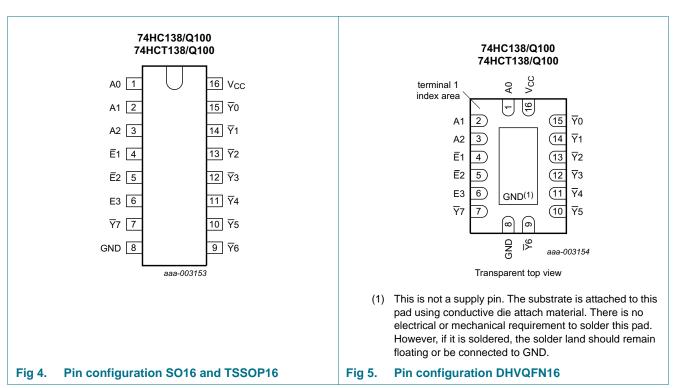
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
A0, A1, A2	1, 2, 3	address input A0, A1, A2
<u>E</u> 1, <u>E</u> 2	4, 5	enable input E1, E2 (active LOW)
E3	6	enable input E3 (active HIGH)
$\overline{Y}0, \overline{Y}1, \overline{Y}2, \overline{Y}3, \overline{Y}4, \overline{Y}5, \overline{Y}6, \overline{Y}7$	15, 14, 13, 12, 11, 10, 9, 7	output $\overline{Y}0$, $\overline{Y}1$, $\overline{Y}2$, $\overline{Y}3$, $\overline{Y}4$, $\overline{Y}5$, $\overline{Y}6$, $\overline{Y}7$ (active LOW)
GND	8	ground (0 V)
V _{CC}	16	positive supply voltage

6. Functional description

Table 3. Function table[1]

Contr	ol		Input			Outp	ut						
<u>E</u> 1	E2	E3	A2	A 1	A0	<u>Y</u> 7	Y 6	Y 5	Y 4	Y 3	Y 2	Y 1	Y 0
Н	Х	Х	Х	Х	Х	Н	Н	Н	Н	Н	Н	Н	Н
Χ	Н	Х											
Χ	Х	L											
L	L	Н	L	L	L	Н	Н	Н	Н	Н	Н	Н	L
			L	L	Н	Н	Н	Н	Н	Н	Н	L	Н
			L	Н	L	Н	Н	Н	Н	Н	L	Н	Н
			L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н
			Н	L	L	Н	Н	Н	L	Н	Н	Н	Н
			Н	L	Н	Н	Н	L	Н	Н	Н	Н	Н
			Н	Н	L	Н	L	Н	Н	Н	Н	Н	Н
			Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$		-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$		-	±25	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-	-50	mA
T _{stg}	storage temperature		-	-65	+150	°C
P _{tot}	total power dissipation		<u>[1]</u> .	-	500	mW

^[1] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
For TSSOP16 package: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
For DHVQFN16 package: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74H	IC138-Q	100	74HCT138-Q100			Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{ar}	_{nb} = 25	°C		40 °C to 5 °C		-40 °C to 5 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC13	B-Q100									
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_{O} = -20 \mu A; V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	5.9	-	٧
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	٧
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	٧
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	٧
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-					pF
74HCT1	38-Q100			1	1	1				
V_{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	8.0	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	bol Parameter Conditions		T _{ar}	T _{amb} = 25 °C			T _{amb} = -40 °C to +85 °C		40 °C to 5 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	$\begin{aligned} &V_I = V_{CC} - 2.1 \text{ V;} \\ &\text{other inputs at } V_{CC} \text{ or GND;} \\ &V_{CC} = 4.5 \text{ V to } 5.5 \text{ V;} \\ &I_O = 0 \text{ A} \end{aligned}$								
		per input pin; An inputs	-	150	540	-	675	-	735	μΑ
		per input pin; En inputs	-	125	450	-	562.5	-	612.5	μΑ
		per input pin; E3 input	-	100	360	-	450	-	490	μΑ
Cı	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions	T _{an}	_{nb} = 25	°C		- –40 °C 85 °C		-40 °C 125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC138	3-Q100									
t _{pd}	propagation	An to Yn; see Figure 6 [1]								
	delay	V _{CC} = 2.0 V	-	41	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	15	30	-	38	-	45	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	12	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	12	26	-	33	-	38	ns
		E3 to Yn; see Figure 6 [1]								
		V _{CC} = 2.0 V	-	47	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	17	20	-	38	-	45	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	38	ns
		$\overline{\text{En to }}\overline{\text{Yn}}; \text{ see } \underline{\text{Figure 7}} $								
		V _{CC} = 2.0 V	-	47	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	17	20	-	38	-	45	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	38	ns
t _t	transition time	Yn; see Figure 6 and Figure 7								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions		Tam	_{ab} = 25	°C		= –40 °C 85 °C		= –40 °C 125 °C	Unit
			N	/lin	Тур	Max	Min	Max	Min	Max	
C _{PD}	power dissipation capacitance	$C_L = 50 \text{ pF; } f = 1 \text{ MHz;}$ $V_I = \text{GND to } V_{CC}$		-	67	-	-	-	-	-	pF
74HCT1	38-Q100							1			
t _{pd}	propagation	An to \overline{Y} n; see Figure 6	1]								
	delay	V _{CC} = 4.5 V		-	20	35	-	44	-	53	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	17	-	-	-	-	-	ns
		E3 to Yn; see Figure 6	1]								
		V _{CC} = 4.5 V		-	18	40	-	50	-	60	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	19	-	-	-	-	-	ns
		En to Yn; see Figure 7	1]								
		V _{CC} = 4.5 V		-	19	40	-	50	-	60	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	19	-	-	-	-	-	ns
t _t	transition time	Yn; see Figure 6 and Figure 7	2]								
		V _{CC} = 4.5 V		-	7	15	-	19	-	22	ns
C _{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC} - 1.5 \text{ V}$	3]	-	67	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

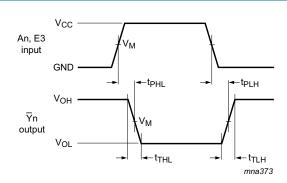
 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

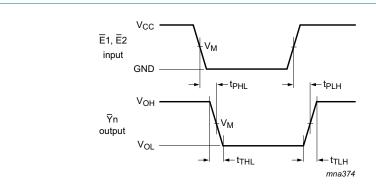
11. Waveforms



Measurement points are given in Table 8.

 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical voltage output levels that occur with the output load.

Fig 6. Propagation delay input (An) and enable input (E3) to output $(\overline{Y}n)$ and transition time output $(\overline{Y}n)$



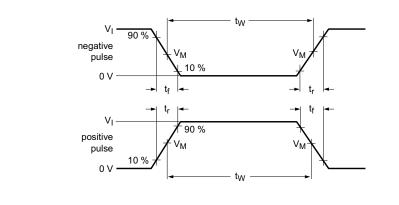
Measurement points are given in Table 8.

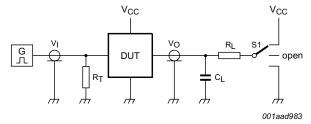
V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Propagation delay enable input (En) to output (Yn) and transition time output (Yn)

Table 8. Measurement points

Туре	Input	Output
	V _M	V _M
74HC138-Q100	0.5V _{CC}	0.5V _{CC}
74HCT138-Q100	1.3 V	1.3 V





Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

 R_L = Load resistance.

S1 = Test selection switch.

Fig 8. Test circuit for measuring switching times

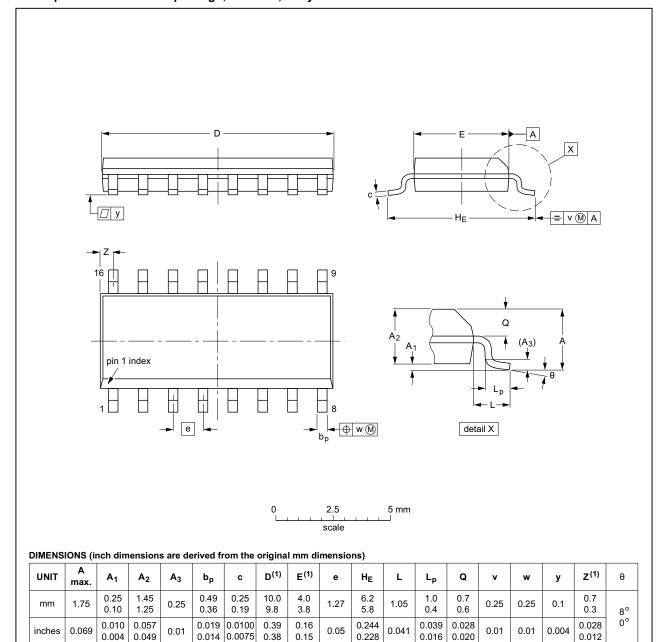
Table 9. Test data

Туре	Input		Load		S1 position				
	VI	t _r , t _f	CL	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
74HC138-Q100	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		
74HCT138-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012			99-12-27 03-02-19

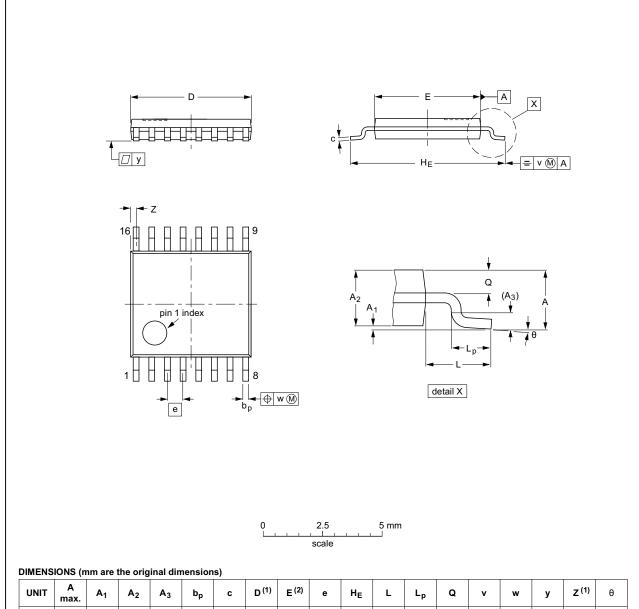
Fig 9. Package outline SOT109-1 (SO16)

74HC_HCT138_Q100

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



- ···-································																		
UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT403-1		MO-153				99-12-27 03-02-18	

Fig 10. Package outline SOT403-1 (TSSOP16)

74HC_HCT138_Q100

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

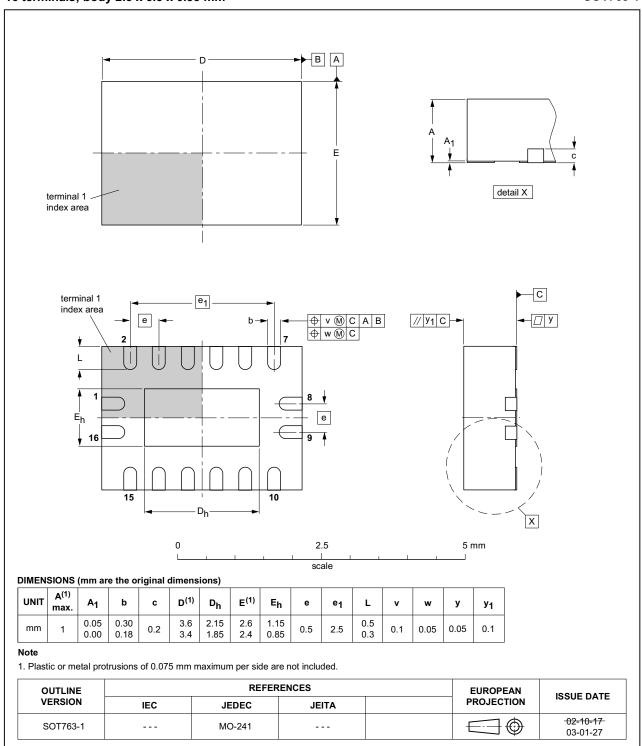


Fig 11. Package outline SOT763-1 (DHVQFN16)

74HC_HCT138_Q100

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
TTL	Transistor-Transistor Logic
MM	Machine Model
MIL	Military

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74HC_HCT138_Q100 v.2	20150126	Product data sheet	-	74HC_HCT138_Q100 v.1		
Modifications:	• <u>Table 6</u> : OFF-9	state output current remov	ed because device	nas no 3-state outputs.		
	• <u>Table 7</u> : Power dissipation capacitance condition for 74HCT138-Q100 is corrected.					
74HC_HCT138_Q100 v.1	20120716	Product data sheet	-	-		

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition					
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.					
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.					
Product [short] data sheet	Production	This document contains the product specification.					

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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